Product data sheet

1. General description

Ultrafast power diode in a TO247-2L plastic package.



2. Features and benefits

- 650V FRD
- Low thermal resistance
- Low forward voltage drop
- Low leakage current & reverse recovery current
- Enhanced Eas capability suitable for industrical application
- Reduces switching losses in associated MOSFET or IGBT
- Package meets UL94 V-0 which guaranteed by Epoxy Mold Compound

3. Applications

- NPC-I in UPS
- · LLC in EV charger
- PFC in air conditioner or welding machine
- Power Factor Correction (PFC)
- 2nd rectification in HB/FB SMPS

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Val	ues		Unit
Absolute maximum rating							
V_{RRM}	repetitive peak reverse voltage			6	50		V
I _{F(AV)}	average forward current	δ = 0.5; $T_{mb} \le$ 123 °C; square-wave pulse; Fig. 1; Fig. 2; Fig. 3		5	50		А
I _{FRM}	repetitive peak forward current	δ = 0.5; t _p = 25 μs; T _{mb} ≤ 123 °C; square-wave pulse	100			А	
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	600		Α		
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse		60	60		А
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static ch	aracteristics						
V _F	forward voltage	I _F = 50 A; T _j = 25 °C; <u>Fig. 6</u>		-	1.35	1.70	V
		I _F = 50 A; T _j = 150 °C; <u>Fig. 6</u>		-	1.05	1.40	V
Dynamic	characteristics				,		
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 100 \text{ A/}\mu\text{s}$; $T_j = 25 \text{ °C}$; Fig. 7		-	38	-	ns

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode		K — A
2	А	anode		001aaa020
mb	mb	mounting base; connected to cathode	K A TO247-2L	

6. Ordering information

Table 3. Ordering information

Type number	Package Name	Orderable part number		Small packing quantity	•	Package issue date
BYV50MW-650PT2	TO247-2L	BYV50MW-650PT2Q	Tube	30	TO247L-2L	10-Nov-2020

7. Marking

Table 4. Marking codes

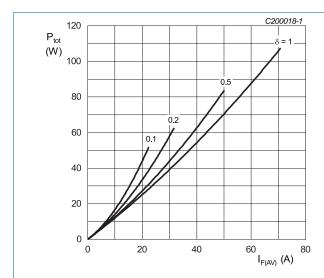
Type number	Marking codes
BYV50MW-650PT2	BYV50MW 650PT2

8. Limiting values

Table 5. Limiting values

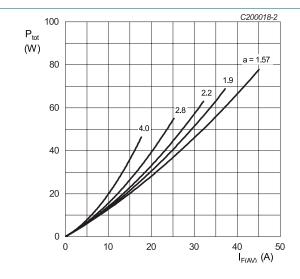
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
V_{RRM}	repetitive peak reverse voltage		650	V
V_{RWM}	crest working reverse voltage		650	V
V_R	reverse voltage	DC	650	V
$I_{F(AV)}$	average forward current	$δ = 0.5$; $T_{mb} \le 123$ °C; square-wave pulse; Fig. 1; Fig. 2; Fig. 3	50	А
I _{FRM}	repetitive peak forward current	δ = 0.5; t _p = 25 μs; T _{mb} ≤ 123 °C; square-wave pulse	100	А
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	600	А
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse	660	А
l ² t	I ² t for fusing	t _p = 10 ms; sine-wave pulse	1800	A ² s
T _{stg}	storage temperature		-65 to 175	°C
T _j	junction temperature		-65 to 175	°C



$$\begin{split} I_{\text{F(AV)}} &= I_{\text{F(RMS)}} \times \sqrt{\delta} \\ V_{\text{o}} &= 1.149 \text{ V; } R_{\text{s}} = 0.0052 \text{ } \Omega \end{split}$$

Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values



a = form factor = $I_{F(RMS)}/I_{F(AV)}$ V_o = 1.149 V; R_s = 0.0052 Ω

Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

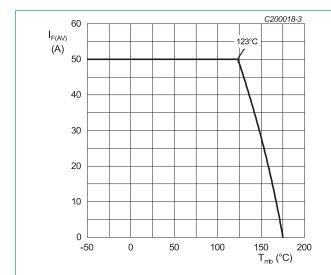


Fig. 3. Average forward current as a function of mounting base temperature; maximum values

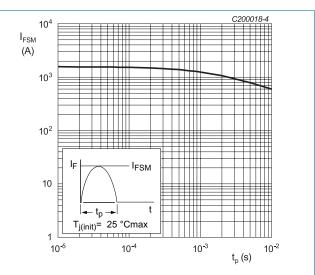


Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 5	-	-	0.62	K/W
$R_{\text{th(j-a)}}$	thermal resistance from junction to ambient free air	in free air	-	40	-	K/W

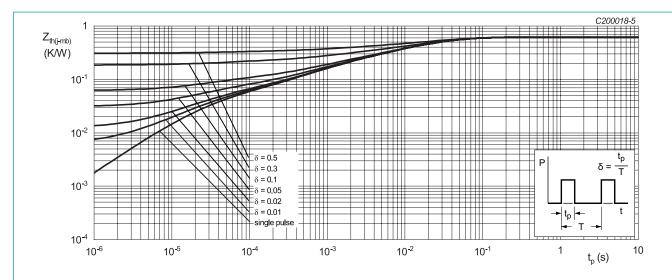
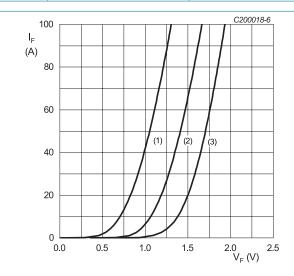


Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration; maximum values

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
V_{F}	forward voltage	$I_F = 50 \text{ A}; T_j = 25 \text{ °C}; Fig. 6$	-	1.35	1.70	V
		I _F = 50 A; T _j = 150 °C; <u>Fig. 6</u>	-	1.05	1.40	V
I _R	reverse current	V _R = 650 V; T _j = 25 °C	-	3	30	μA
		V _R = 650 V; T _j = 150 °C	-	-	2	mA
Dynamic	characteristics			'		
t _r	reverse recovery time	$I_F = 0.5 \text{ A}; I_R = 1 \text{ A}; I_{rr} = 0.25 \text{ A};$ $T_j = 25 \text{ °C}$	-	52	-	ns
		$I_F = 1 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 100 \text{ A/}\mu\text{s}$; $T_j = 25 \text{ °C}$; Fig. 7	-	38	-	ns
		$I_F = 50 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 500 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	65	-	ns
		$I_F = 50 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 500 \text{ A}/\mu\text{s};$ $T_j = 125 ^{\circ}\text{C}; Fig. 7$	-	120	-	ns
I _{RM}	peak reverse recovery current	$I_F = 50 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 500 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; \frac{\text{Fig. 7}}{}$	-	16.5	-	А
		$I_F = 50 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 500 \text{ A/}\mu\text{s};$ $T_j = 125 ^{\circ}\text{C}; Fig. 7$	-	32	-	А
Q _r	recovered charge	$I_F = 50 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 500 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; \frac{\text{Fig. 7}}{}$	-	530	-	nC
		$I_F = 50 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 500 \text{ A}/\mu\text{s};$ $T_j = 125 ^{\circ}\text{C}; \underline{\text{Fig. 7}}$	-	1900	-	nC
Eas	non-repetitive analanche energy	T _j = 25 °C	46	-	-	mJ





⁽²⁾ T_i = 150 °C; maximum values

Fig. 6. Forward current as a function of forward voltage

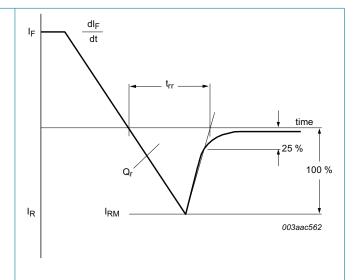
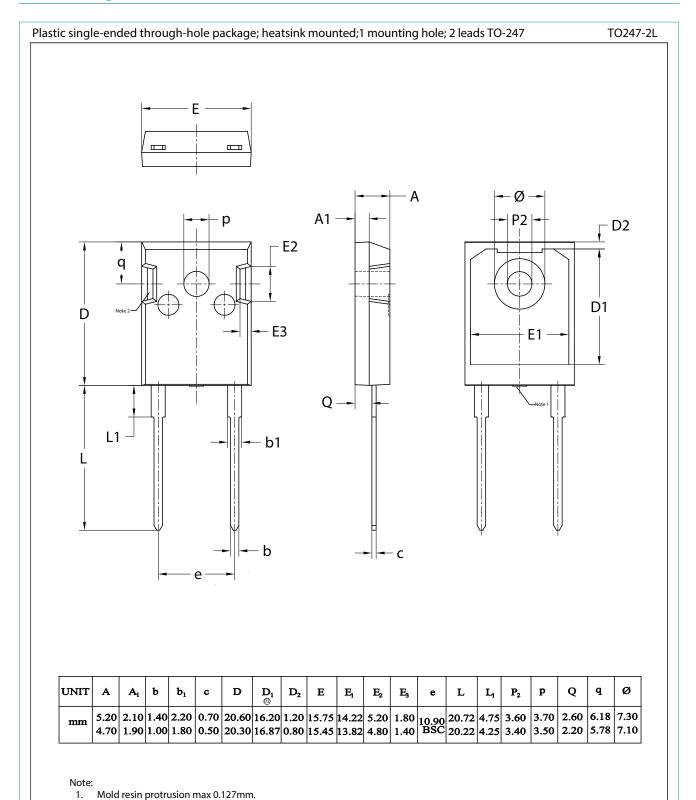


Fig. 7. Reverse recovery definitions; ramp recovery

⁽³⁾ $T_j = 25$ °C; maximum values

 $V_o = 1.149 \text{ V}; R_s = 0.0052 \Omega$

11. Package outline



Metal exposed with Sn plating.

12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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